

Daniel Feezell

List of Publications by Year in descending order

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Version: 2024-02-01

27
papers

1,268
citations

430754

18
h-index

552653

26
g-index

27
all docs

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docs citations

27
times ranked

1260
citing authors

#	ARTICLE	IF	CITATIONS
1	High-Power Blue-Violet Semipolar (20×10^4) InGaN/GaN Light-Emitting Diodes with Low Efficiency Droop at 200 A/cm^2 . Applied Physics Express, 2011, 4, 082104.	1.1	177
2	Indium incorporation and emission properties of nonpolar and semipolar InGaN quantum wells. Applied Physics Letters, 2012, 100, .	1.5	168
3	High-Power, Low-Efficiency-Droop Semipolar (20×10^4) Single-Quantum-Well Blue Light-Emitting Diodes. Applied Physics Express, 2012, 5, 062103.	1.1	102
4	Nonpolar m -Plane InGaN/GaN Micro-Scale Light-Emitting Diode With 1.5 GHz Modulation Bandwidth. IEEE Electron Device Letters, 2018, 39, 520-523.	2.2	93
5	Invention, development, and status of the blue light-emitting diode, the enabler of solid-state lighting. Comptes Rendus Physique, 2018, 19, 113-133.	0.3	89
6	High optical polarization ratio from semipolar (20×10^4) blue-green InGaN/GaN light-emitting diodes. Applied Physics Letters, 2011, 99, .	1.5	75
7	High-Speed Nonpolar InGaN/GaN LEDs for Visible-Light Communication. IEEE Photonics Technology Letters, 2017, 29, 381-384.	1.3	67
8	Influence of polarity on carrier transport in semipolar (20×10^4) and (20×10^4) multiple-quantum-well light-emitting diodes. Applied Physics Letters, 2012, 100, .	1.5	54
9	A Decade of Nonpolar and Semipolar III-Nitrides: A Review of Successes and Challenges. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800628.	0.8	54
10	Electrically Injected GHz-Class GaN/InGaN Core-Shell Nanowire-Based LEDs: Carrier Dynamics and Nanoscale Homogeneity. ACS Photonics, 2019, 6, 1618-1625.	3.2	52
11	Si-doped $\text{In}_{0.26}\text{Ga}_{0.74}\text{O}_3$ thin films and heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2019, 12, 111004.	1.1	47
12	Reduction in Thermal Droop Using Thick Single-Quantum-Well Structure in Semipolar (20×10^4) Blue Light-Emitting Diodes. Applied Physics Express, 2012, 5, 102103.	1.1	41
13	Delta-doped $\text{In}_{0.26}\text{Ga}_{0.74}\text{O}_3$ thin films and $\text{In}_{0.26}\text{Ga}_{0.74}\text{O}_3/\text{In}_{0.26}\text{Ga}_{0.74}\text{O}_3$ heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2020, 13, 045501.		
14	Optical polarization characteristics of semipolar (30×10^4) and (30×10^4) InGaN/GaN light-emitting diodes. Optics Express, 2013, 21, A53.	1.7	35
15	Optical properties of nonpolar III-nitrides for intersubband photodetectors. Journal of Applied Physics, 2013, 113, .	1.1	34
16	Explanation of low efficiency droop in semipolar (20×10^4) InGaN/GaN LEDs through evaluation of carrier recombination coefficients. Optics Express, 2017, 25, 19343.	1.7	34
17	Influence of Mg-doped barriers on semipolar (20×10^4) multiple-quantum-well green light-emitting diodes. Applied Physics Letters, 2011, 99, 141114.	1.5	21
18	Thermal and efficiency droop in InGaN/GaN light-emitting diodes: decoupling multiphysics effects using temperature-dependent RF measurements. Scientific Reports, 2019, 9, 19921.	1.6	19

#	ARTICLE	IF	CITATIONS
19	Optical properties of Ag-coated GaN/InGaN axial and core-shell nanowire light-emitting diodes. Journal of Optics (United Kingdom), 2015, 17, 025004.	1.0	14
20	Interfacial Impurities and Their Electronic Signatures in High-Voltage Regrown Nonpolar m-Plane GaN Vertical Schottky Diodes. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900757.	0.8	14
21	Experimental study of field emission from ultrasharp silicon, diamond, GaN, and tungsten tips in close proximity to the counter electrode. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, .	0.6	13
22	Insufficiency of the Young's modulus for illustrating the mechanical behavior of GaN nanowires. Nanotechnology, 2018, 29, 205706.	1.3	11
23	Analysis of light extraction efficiency for gallium nitride-based coaxial microwall light-emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 766-770.	0.8	5
24	Sharp GaN nanowires used as field emitter on active cantilevers for scanning probe lithography. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, .	0.6	5
25	Defect suppression in wet-treated etched-and-regrown nonpolar m-plane GaN vertical Schottky diodes: A deep-level optical spectroscopy analysis. Journal of Applied Physics, 2020, 128, 185703.	1.1	3
26	Field emission scanning probe lithography with GaN nanowires on active cantilevers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, 032806.	0.6	3
27	Carrier Dynamics in InGaN/GaN Micro-LEDs: An RF Approach to Understand Efficiency Issues. , 2019, , .		0